

**Amendments to the Specification:**

Please replace the paragraphs beginning on page 10, line 13, with the following rewritten paragraphs:

Fig. 8 depicts a flow chart illustrating an embodiment of a method for determining a thickness of an insulating film formed on a substrate; and

Fig. 9 depicts a flow chart illustrating an embodiment of a method for determining a property of an insulating film formed on a substrate; and

~~Fig. 10 depicts a plot of  $Q-V$  and  $C-V$  data measured on an imperfectly insulating  $\text{SiO}_2$  film.~~

Please replace the paragraph beginning on page 27, line 7, with the following rewritten paragraph:

~~Fig. 10 illustrates a plot of  $Q-V$  and  $C-V$  data was measured on an imperfectly insulating  $\text{SiO}_2$  film. As shown in Fig. 10, less Less leakage is was present near zero electric field across the  $\text{SiO}_2$  film thereby resulting in improved performance. This reduced leakage is was easily seen by ~~the~~ a minimum (absolute value) in the slope of the  $C-V$  data at a voltage of approximately 0 V ~~as denoted by the vertical marker line.~~~~

By making measurements in this non-traditional voltage or electric field regime, the effects of leakage, whether modeled or not, may be reduced, and superior performance may be achieved.